

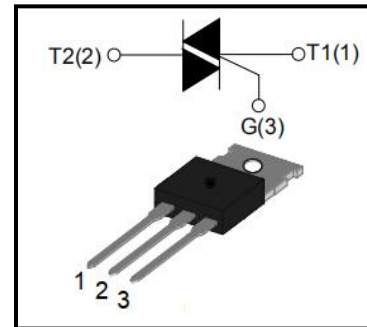
P/N: YZPST-TYN616

● Package

T0-220C

● Main Feature (Tj=25°C)

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM} / V_{RRM}	600	V
I_{GT}	2 to 15	mA



T0-220C

● Absolute ratings (Limiting Values)

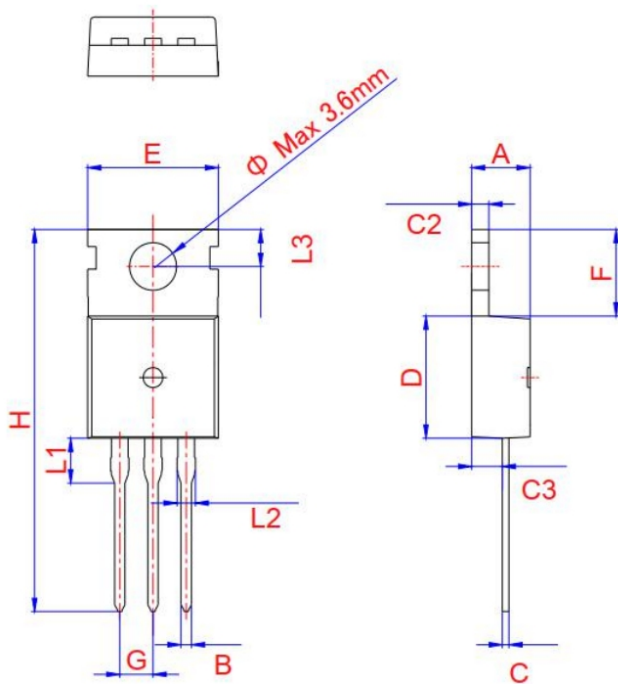
Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	16	A
$I_{T(AV)}$	AV on-state current (180° conduction angle)	10	A
I_{TSM}	Non repetitive surge peak on-state Current (tp=10ms)	160	A
I^2t	(tp=10ms)	100	A ² S
I_{GM}	Peak gate current(tp=20us)	4	A
P_{GM}	Peak gate power	5	W
$P_{G(AV)}$	Average gate power	1	W
Tstg	Storage temperature	-40--+150	°C
Tj	Operating junction temperature	-40--+125	

● Thermal Resistances

Symbol	Parameter	Value	Unit
Rth (j-c)	Junction to case	1.1	K/W
Rth (j-a)	Junction to ambient	55	K/W

●Electrical characteristics (T_j=25°C unless otherwise stated)

Symbol	Test Conditions		Value			Unit
			Min	Type	Max	
I _{GT}	V _D =6V, R _L =100 Ω		2	5	15	mA
V _{GT}	V _D =12V, R _L =100 Ω		-----	0.7	0.8	V
V _{GD}	V _D =V _{DRM} , R _L =3.3K Ω T _j =110°C		0.2	-----	-----	V
I _H	I _T =100mA Gate Open		-----	30	40	mA
dV/dt	V _D =67%V _{DRM} , GateOpen, T _j =125°C		400	-----	-----	v/ μ s
V _{TM}	I _T =24A, t _p =380 μ s		-----	-----	1.7	V
I _{DRM}	V _D =V _{DRM}	T _j =25°C	-----	-----	10	uA
I _{RRM}	V _R =V _{RRM}	T _j =125°C	-----	-----	1	mA

●Measure of package

TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.3		4.5	0.169		0.177
B	0.7		0.9	0.028		0.035
C	0.45		0.6	0.018		0.024
C2	1.23	1.30	1.32	0.048	0.051	0.052
C3	2.2		2.6	0.087		0.102
D	8.9		9.9	0.35		0.39
E	9.9	10.1	10.3	0.39	0.398	0.406
F	6.3		6.9	0.248		0.272
G		2.54			0.1	
H	28		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.7	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	